

N-channel TrenchMOS logic level FET

13 July 2012

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | - | 100 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 234 | W |
| Static charac | teristics | · | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u> | | - | 2.6 | 3.1 | mΩ |
| Dynamic cha | racteristics | · | | | | | |
| Q _{GD} | gate-drain charge | V _{GS} = 5 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14 | | - | 25.8 | - | nC |

[1] Continuous current is limited by package.

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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G - LET T |
| mb | D | mounting base; connected to drain | D2PAK (SOT404) | mbb076 S |

3. Ordering information

| Table 3. Ordering inf | formation | | |
|-----------------------|-----------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| BUK963R1-40E | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|-------------------------|--|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 40 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | | - | 40 | V |
| V _{GS} | gate-source voltage | T _j = 25 °C | | -10 | 10 | V |
| | | $T_j = 25 \text{ °C};$ lifetime = 100 hours | | -15 | 15 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u> | [1] | - | 100 | А |
| | | T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u> | [1] | - | 100 | А |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4 | | - | 794 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 234 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-dra | in diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 100 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 794 | А |

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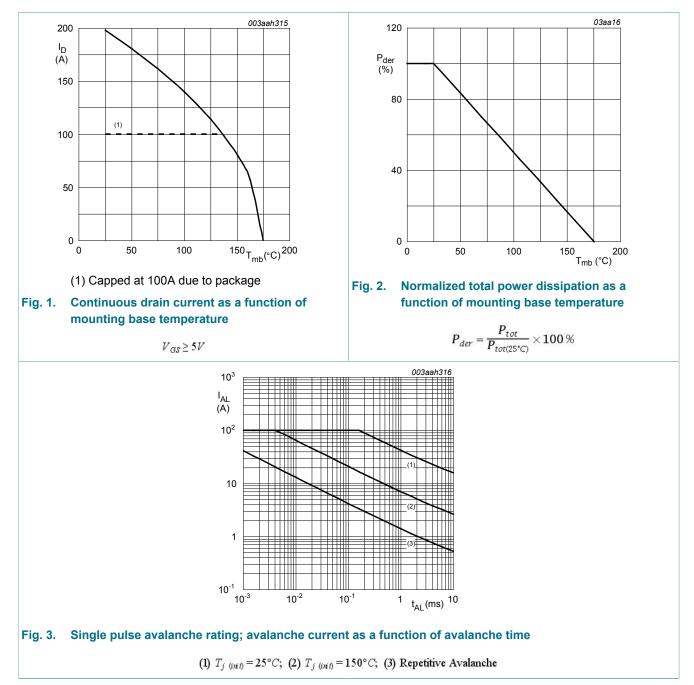
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| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|----------------------|---|---|----------------|-----|-----|------|
| Avalanche rug | gedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\begin{split} I_D &= 100 \text{ A}; \text{ V}_{sup} \leq 40 \text{ V}; \text{ R}_{GS} = 50 \Omega; \\ \text{V}_{GS} &= 5 \text{ V}; T_{j(init)} = 25 \text{ °C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$ | [<u>2][3]</u> | - | 419 | mJ |

[1]

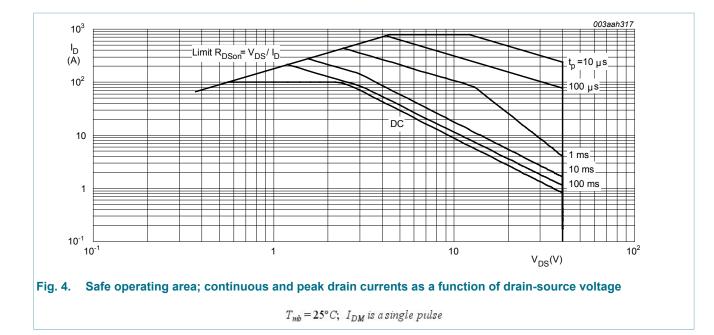
Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.



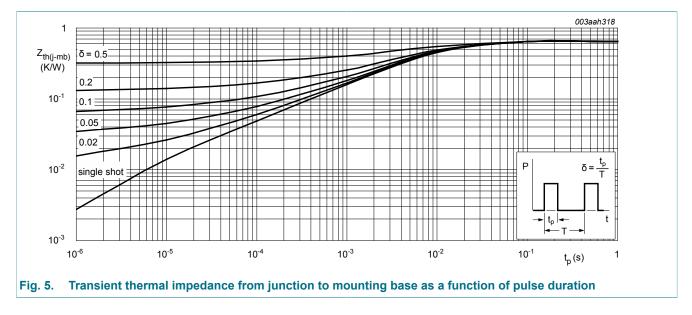
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5. Thermal characteristics

| Table 5. The | rmal characteristics | | | | | |
|-----------------------|---|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | - | 0.64 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed-circuit board | - | 50 | - | K/W |



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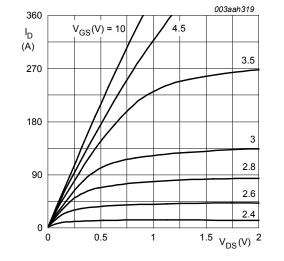
6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|--|------|------|------|------|
| Static chara | acteristics | · · · · | I | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 40 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 36 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10 | 1.4 | 1.7 | 2.1 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 2.45 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9 | 0.5 | - | - | V |
| I _{DSS} | drain leakage current | V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.06 | 1 | μA |
| | | V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 2.6 | 3.1 | mΩ |
| resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 2.25 | 2.7 | mΩ | |
| | | V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11 | - | - | 6 | mΩ |
| Dynamic cl | naracteristics | · · · · · | | I | 1 | |
| Q _{G(tot)} | total gate charge | I_D = 25 A; V_{DS} = 32 V; V_{GS} = 5 V; | - | 69.5 | - | nC |
| Q _{GS} | gate-source charge | Fig. 13; Fig. 14 | - | 16.1 | - | nC |
| Q _{GD} | gate-drain charge | | - | 25.8 | - | nC |
| C _{iss} | input capacitance | V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; | - | 6870 | 9150 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | - | 875 | 1050 | pF |
| C _{rss} | reverse transfer capacitance | | - | 450 | 620 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V; | - | 42 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | - | 73 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 114 | - | ns |
| t _f | fall time | | - | 76 | - | ns |
| L _D | internal drain inductance | from upper edge of drain mounting base to center of die | - | 2.5 | - | nH |
| L _S | internal source inductance | from source lead to source bonding pad | - | 7.5 | - | nH |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|-----|-----|------|
| Source-drain o | liode | | | | | |
| V _{SD} | source-drain voltage | I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V; | - | 40 | - | ns |
| Q _r | recovered charge | V _{DS} = 25 V | - | 47 | - | nC |



T_j = 25 °C; t_p = 300 μs



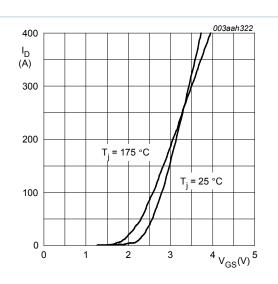


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$

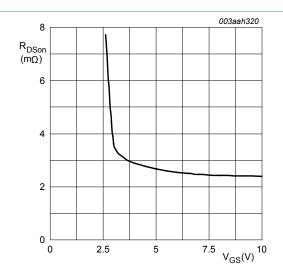


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$

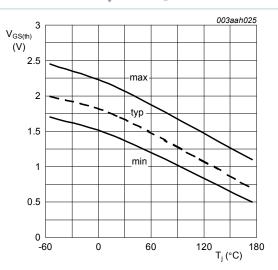
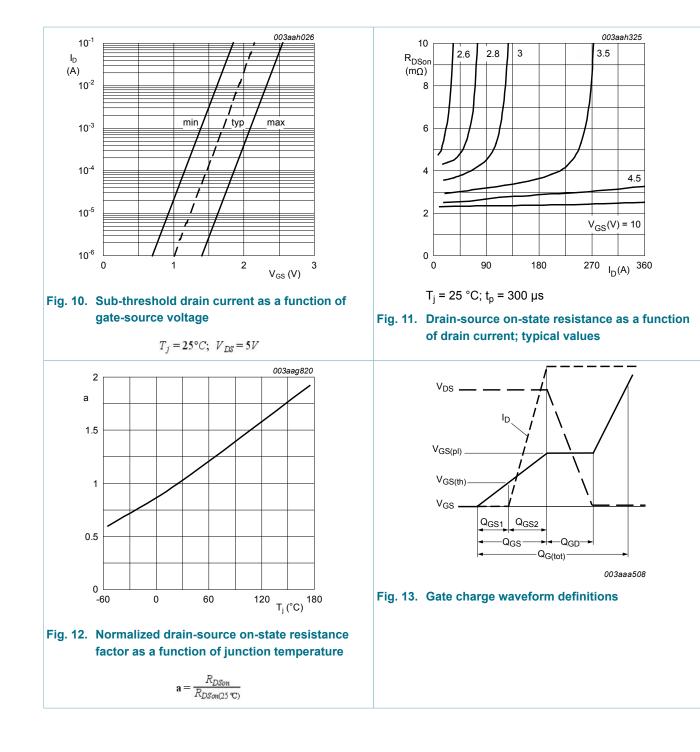


Fig. 9. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

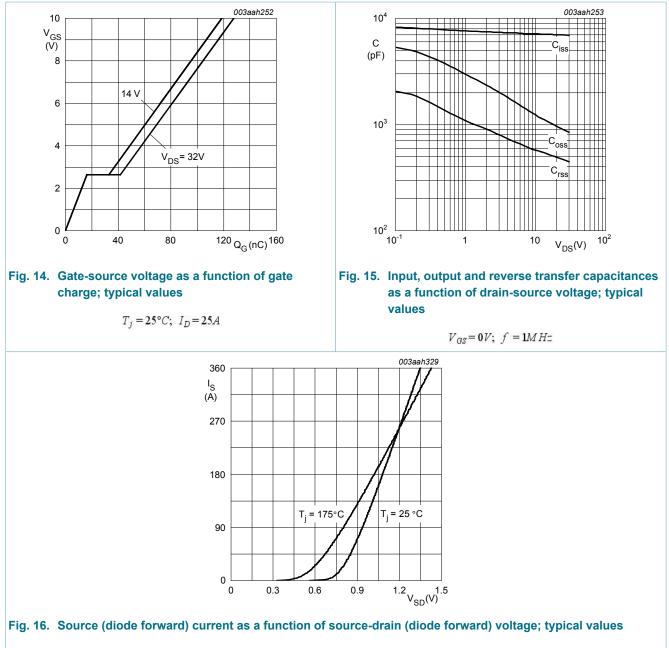
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 $V_{GS} = \mathbf{0} V$

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7. Package outline

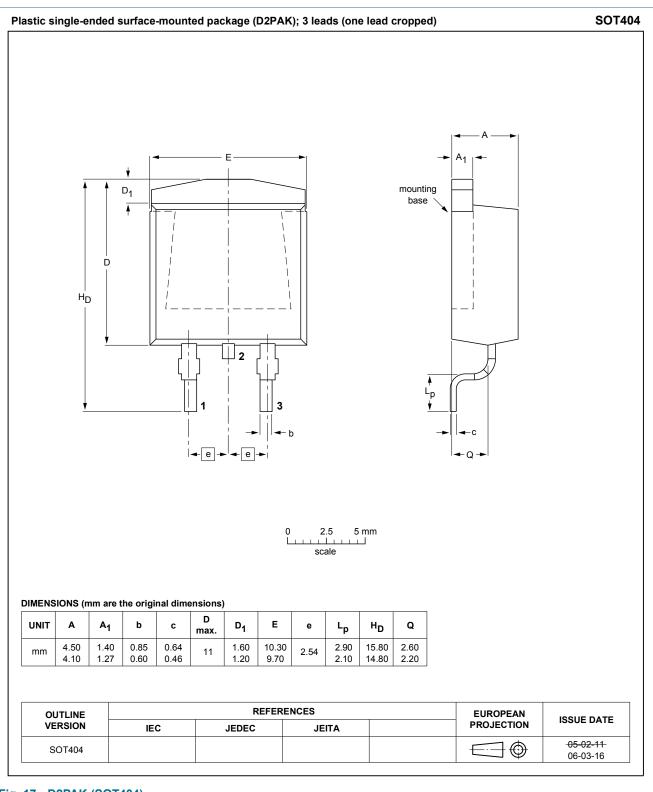


Fig. 17. D2PAK (SOT404)

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|--------------------------------------|-------------------------------|---|
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